Surface Mount - 50V





#### **Additional Information**







Accessories



Samples

### **Description**

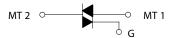
Designed for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications. The MAC8SxG is designed for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

#### **Features**

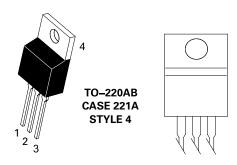
- Sensitive Gate Allows
   Triggering by Microcontrollers
   and other Logic Circuits
- Uniform Gate Trigger Currents in Three Quadrants; Q1, Q2, and Q3
- High Immunity to dv/dt 25 V/µs Minimum at 110°C
- High Commutating di/dt 8.0 A/ms Minimum at 110°C
- Maximum Values of I<sub>GT</sub>, V<sub>GT</sub> and I<sub>H</sub> Specified for Ease of Design

- On-State Current Rating of 8 Amperes RMS at 70°C
- High Surge Current Capability70 Amperes
- Blocking Voltage to 800 Volts
- Rugged, Economical TO-220 Package
- These Devices are Pb-Free and are RoHS Compliant

### **Functional Diagram**



#### **Pin Out**





## MAC8SDG, MAC8SMG, MAC8SNG Surface Mount – 50V

### **Maximum Ratings** (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = 25^{\circ}$ to 110°C)	MAC8SDG MAC8SMG MAC8SNG	V <sub>DRM</sub> , V <sub>RRM</sub>	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 7$ )	0°C)	I <sub>T (RMS)</sub>	8.0	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T,= 110°C)		I <sub>TSM</sub>	70	А
Circuit Fusing Consideration (t = 8.3 ms)		l²t	20	A²sec
Peak Gate Power (Pulse Width $\leq 1.0 \mu s$ , $T_c = 70^{\circ}C$ )		P <sub>GM</sub>	16	W
Average Gate Power (t = $8.3 \text{ ms}$ , $T_c = 70^{\circ}\text{C}$ )		$P_{G(AV)}$	0.35	W
Operating Junction Temperature Range		$T_{J}$	-40 to +110	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 10 seconds	s, 1/8" from case for	T <sub>L</sub>	260	°C

# **Electrical Characteristics - OFF** (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T_ = 25°C	I <sub>DRM</sub> ,	-	-	0.01	m Λ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	$T_{J}^{\circ} = 110^{\circ}C$	I	-	-	2.0	mA

# **Electrical Characteristics - ON** (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On-State Voltage (Note 4) $(I_{TM} = \pm 11 \text{ A})$		$V_{TM}$	_	_	1.85	V
Gate Trigger Current	MT2(+), G(+)		_	2.0	5.0	mA
(Continuous dc)	MT2(+), G(-)	I <sub>GT</sub>	_	3.0	5.0	
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	MT2(-), G(-)		_	3.0	5.0	
Holding Current ( $V_D$ = 12 V, Gate Open, Initiating Current = ±	150 mA))	I <sub>H</sub>	_	3.0	10	mA
Latching Current $(V_D = 24 \text{ V, } I_G = 5 \text{ mA})$	MT2(+), G(+)	I <sub>L</sub>	_	5.0	15	mA
	MT2(+), G(-)		_	10	20	
$(\mathbf{v}_{D} - 2 \cdot \mathbf{v}, \mathbf{v}_{G} - 3 \cdot \mathbf{v}, \mathbf{v}_{G})$	MT2(-), G(-)		_	5.0	15	
0 . T	MT2(+), G(+)		0.45	0.62	1.5	
Gate Trigger Voltage $(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(+), G(-)	$V_{\rm GT}$	0.45	0.60	1.5	V
	MT2(-), G(-)		0.45	0.65	1.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.





<sup>1.</sup> V<sub>Dask</sub> and V<sub>Stack</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

## MAC8SDG, MAC8SMG, MAC8SNG Surface Mount – 50V

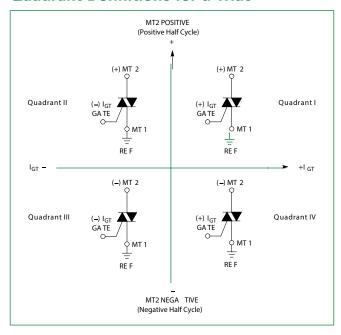
## **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current See Figure 10. ( $V_D = 400 \text{ V}$ , $I_{TM} = 3.5 \text{ A}$ , Commutating dv/dt = 10 V/ $\mu$ s, Gate Open, $T_J = 110^{\circ}$ C, f = 500 Hz, Snubber), $C_S = 0.01 \ \mu$ F, $R_S = 15 \ \Omega$	di/dt <sub>(C)</sub>	8.0	10	_	A/ms
Critical Rate of Rise of Off-State Voltage ( $V_D = Rated V_{DRM}$ , Exponential Waveform, $R_{GK} = 510 \Omega$ , $T_J = 110^{\circ}$ C)	dV/dt	25	75	_	V/µs

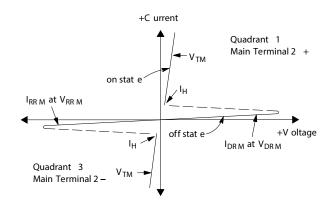
## **Voltage Current Characteristic of SCR**

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{_{\mathrm{RRM}}}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
I <sub>H</sub>	Holding Current

#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1. With in–phase signals (using standard AC lines) quadrants I and III are used



**Figure 1. RMS Current Derating** 

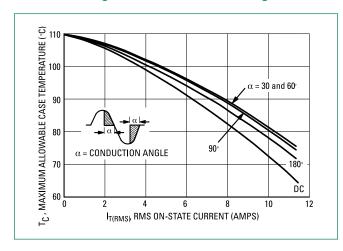


Figure 3. On-State Characteristics

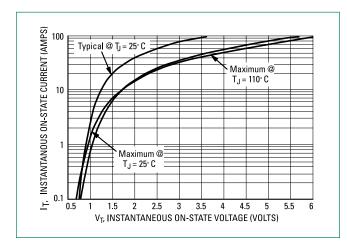


Figure 5. Typical Holding Current Vs. Junction Temperature

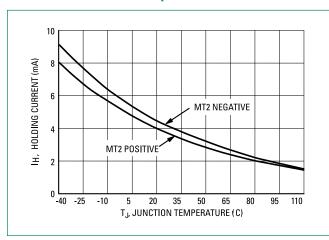
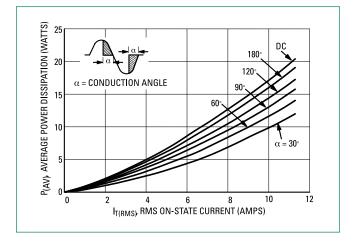


Figure 2. Maximum On-State Power Dissipation



**Figure 4. Transient Thermal Response** 

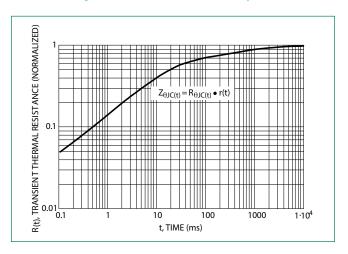
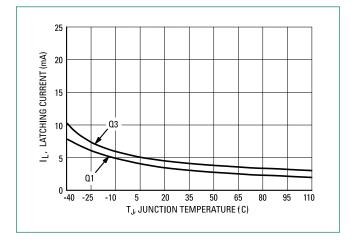


Figure 6. Typical Latching Current Vs. Junction Temperature





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Figure 7. Typical Gate Trigger Current Vs. Junction Temperature

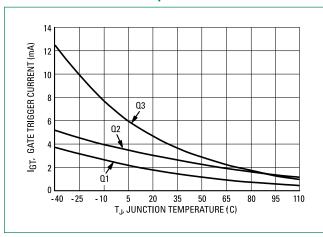


Figure 9. Typical Exponential Static dv/dt Vs. Gate-MT1 Resistance, MT2(+)

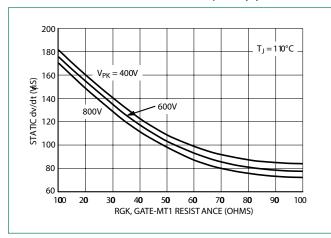


Figure 11. Typical Exponential Static dv/dt Vs. Junction Temperature, MT2(+)

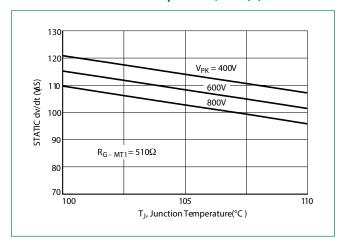


Figure 8. Typical Gate Trigger Voltage Vs. Junction Temperature

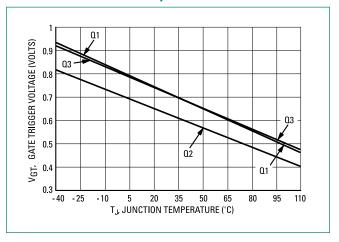


Figure 10. Typical Exponential Static dv/dt Versus Peak Voltage, MT2(+)

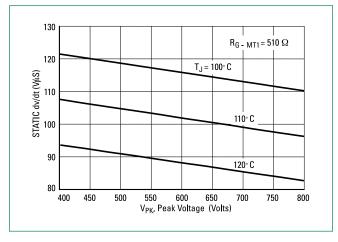
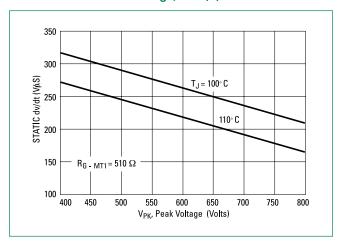


Figure 12. Typical Exponential Static dv/dt Vs. Peak Voltage, MT2(-)





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Figure 13. Typical Exponential Static dv/dt Versus Junction Temperature, MT2(-)

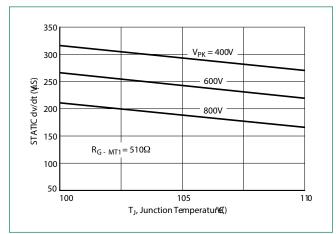


Figure 14. Typical Exponential Static dv/dt Versus Gate-MT1 Resistance, MT2(-)

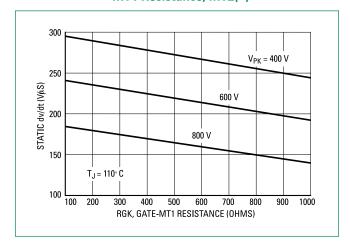


Figure 15. Critical Rate of Rise of Commutating Voltage

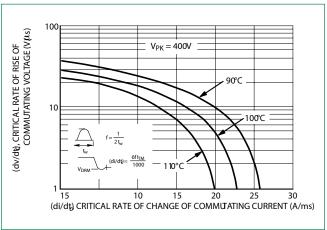
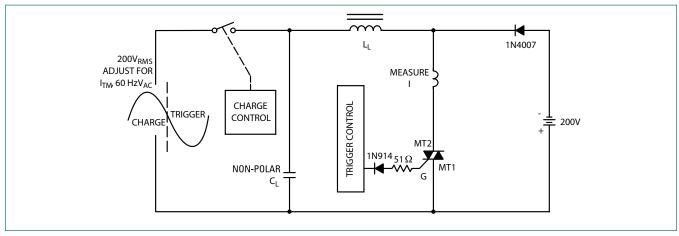


Figure 16. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)

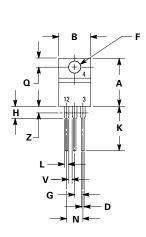


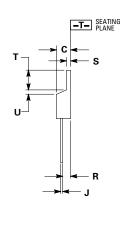
Note: Component values are for verification of rated (di/dt)c. See AN1048 for additional information



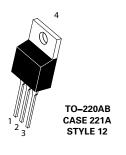
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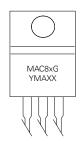
#### **Dimensions**





#### **Part Marking System**





x =D, M, or N Y =Year M =Month

A =Assembly Site
XX =Lot Serial Code

///	- LUL JUII	ai Code
G	=Pb-Free	Package

Dim	Inches		Millimeters		
νim	Min	Max	Min	Max	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
K	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
N	0.195	0.205	4.95	5.21	
Q	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

1	Dimensioning	and	tolorancina	nor	anci v14 Em	1002
١.	Difficusioning	dilu	wierancing	hei	ansi y 14.5m,	1302.

2. Controlling dimension: inch.

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	No Connection			

### **Ordering Information**

Device	Package	Shipping
MAC8SDG	TO 000 1 D	
MAC8SMG	TO-220AB (Pb-Free)	1000 Units / Box
MAC8SNG	(1 5 1100)	





<sup>3.</sup> Dimension z defines a zone where all body and lead irregularities are allowed.

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BTB16Q-600BW Z0409MF BTA04-600B BTA06-600BRG BTA06-800BWRG BTA08-600BRG BTA08-800B BT136-600,127

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